

BUV20

SWITCHMODE™ Series NPN Silicon Power Transistor

SWITCHMODE series NPN silicon power transistors are designed for high speed, high current, high power applications.

- High DC current gain:
 $h_{FE} \text{ min} = 20 \text{ at } I_C = 25 \text{ A}$
 $= 10 \text{ at } I_C = 50 \text{ A}$
- Low $V_{CE(sat)}$:
 $V_{CE(sat)} \text{ max.} = 0.6 \text{ V at } I_C = 25 \text{ A}$
 $= 0.9 \text{ V at } I_C = 50 \text{ A}$
- Very fast switching times:
 $T_F = 0.25 \mu\text{s at } I_C = 50 \text{ A}$

MAXIMUM RATINGS

Rating	Symbol	BUV20	BUV60	Unit
Collector-Emitter Voltage	$V_{CEO(sus)}$	125		Vdc
Collector-Base Voltage	V_{CBO}	160	260	Vdc
Emitter-Base Voltage	V_{EBO}	7		Vdc
Collector-Emitter Voltage ($V_{BE} = -1.5 \text{ V}$)	V_{CEX}	160	260	Vdc
Collector-Emitter voltage ($R_{BE} = 100 \Omega$)	V_{CER}	150	260	Vdc
Collector-Current — Continuous — Peak ($PW \leq 10 \text{ ms}$)	I_C I_{CM}	50 60		Adc Apk
Base-Current continuous	I_B	10		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	250		Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to 200		$^\circ\text{C}$

THERMAL CHARACTERISTICS

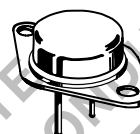
Characteristic	Symbol	BUV20	BUV60	Unit
Thermal Resistance, Junction to Case	θ_{JC}	0.7		$^\circ\text{C/W}$



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**50 AMPERES
NPN SILICON POWER
METAL TRANSISTOR
125 VOLTS, 250 WATTS**



CASE 197A-05
TO-204AE
(TO-3)

BUV20

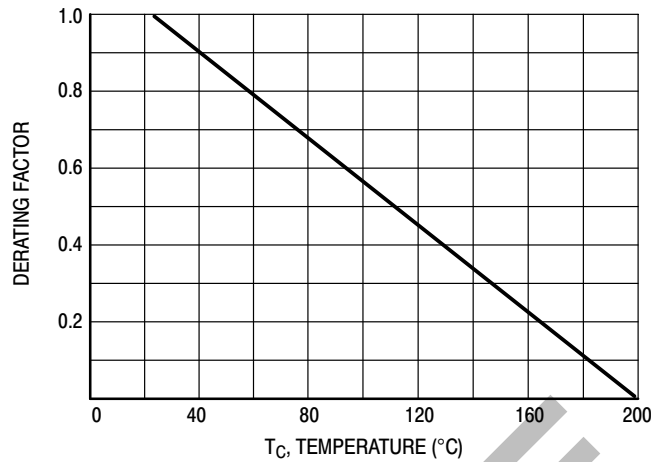


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS¹

Collector–Emitter Sustaining Voltage (I _C = 200 mA, I _B = 0, L = 25 mH)	BUV20, BUV60	V _{CEO(sus)}	125		Vdc
Collector Cutoff Current at Reverse Bias (V _{CE} = 140 V, V _{BE} = -1.5 V)	BUV20	I _{CEX}		3.0	mAdc
(V _{CE} = 140 V, V _{BE} = -1.5 V, T _C = 125°C)	BUV20			12	
(V _{CE} = 260 V, V _{BE} = -1.5 V)	BUV60				
Collector–Emitter Cutoff Current (V _{CE} = 100 V)	BUV20	I _{CEO}		3.0	mAdc
Emitter–Base Reverse Voltage (I _E = 50 mA)	BUV20, BUV60	V _{EBO}	7		V
Emitter–Cutoff Current (V _{EB} = 5 V)	BUV20, BUV60	I _{EBO}		1.0	mAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with base forward biased (V _{CE} = 20 V, t = 1 s)		I _{S/b}	12		Adc
(V _{CE} = 40 V, t = 1 s)			1.5		

ON CHARACTERISTICS¹

DC Current Gain (I _C = 25 A, V _{CE} = 2 V)	BUV20	h _{FE}	20	60	
(I _C = 50 A, V _{CE} = 4 V)	BUV20		10	-	
Collector–Emitter Saturation Voltage (I _C = 25 A, I _B = 2.5 A)	BUV20	V _{CE(sat)}		0.6	Vdc
(I _C = 50 A, I _B = 5 A)	BUV20			1.2	
Base–Emitter Saturation Voltage (I _C = 50 A, I _B = 5 A)0	BUV20	V _{BE(sat)}		2.0	Vdc
Collector–Emitter Saturation Voltage (I _C = 25 A, I _B = 1.25 A)	BUV60	V _{CE(sat)}		0.9	Vdc
(I _C = 50 A, I _B = 5 A)	BUV60			0.9	
(I _C = 60 A, I _B = 7.5 A)	BUV60			1.2	
Base–Emitter Saturation Voltage (I _C = 50 A, I _B = 5 A)	BUV60	V _{BE(sat)}		1.6	Vdc
(I _C = 60 A, I _B = 7.5 A)	BUV60			1.8	

DYNAMIC CHARACTERISTICS

Current Gain — Bandwidth Product (V _{CE} = 15 V, I _C = 2 A, f = 4 MHz)		f _T	8.0		MHz
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BUV20

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS (Resistive Load)				
Turn-on Time	$(I_C = 50\text{ A}, I_{B1} = I_{B2} = 5\text{ A}, V_{CC} = 30\text{ V}, R_C = 0.6\ \Omega)$	t_{on}	1.5	μs
Storage Time		t_s	1.2	
Fall Time		t_f	0.25	

¹ Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

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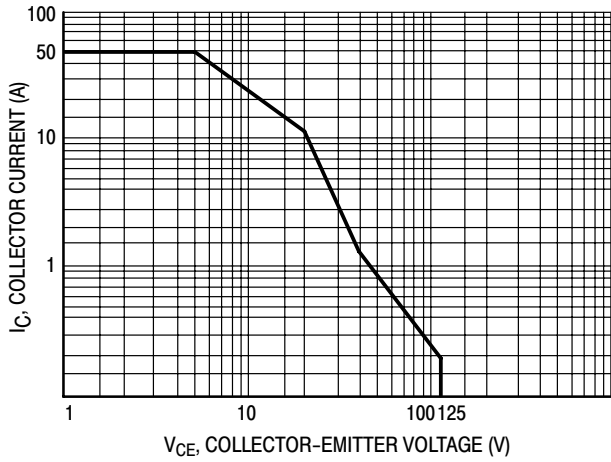


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^\circ\text{C}$. $T_{J(pk)}$ is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

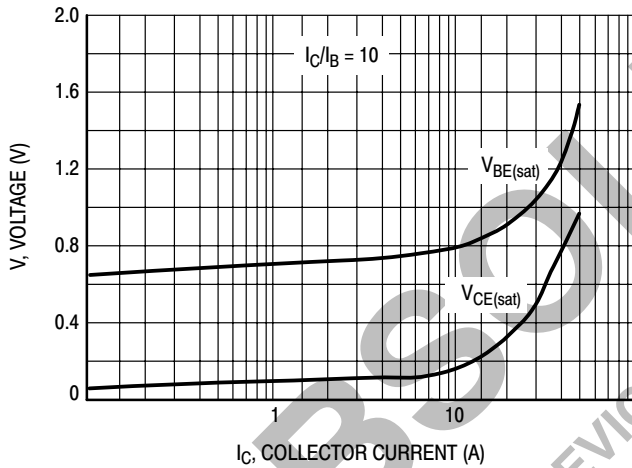


Figure 3. "On" Voltages

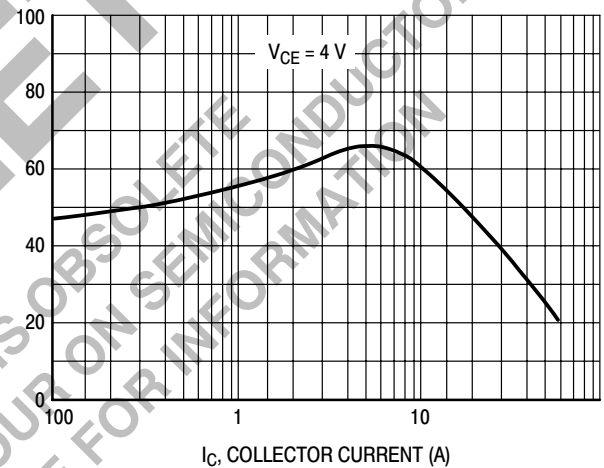


Figure 4. DC Current Gain

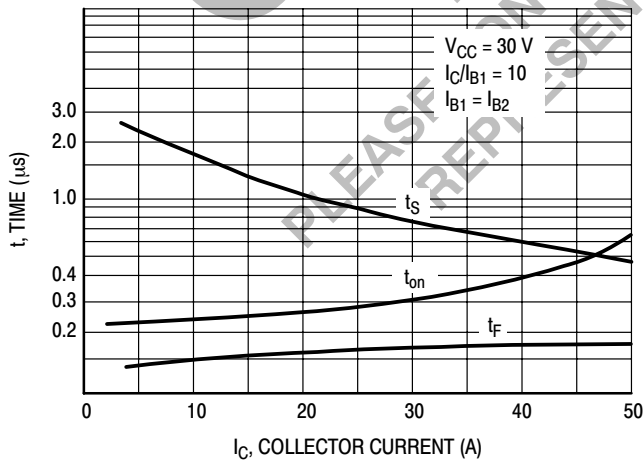


Figure 5. Resistive Switching Performance

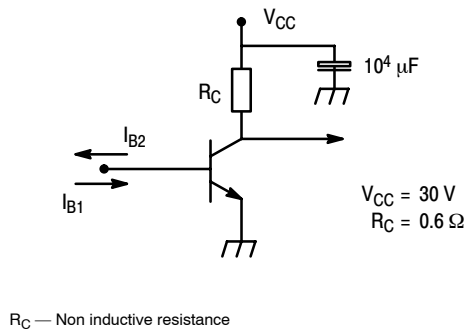
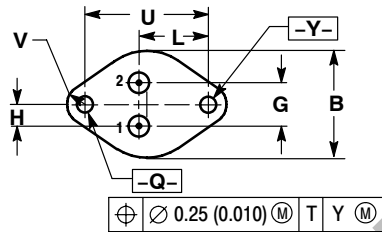
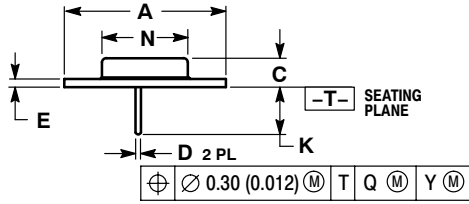


Figure 6. Switching Times Test Circuit

BUV20

PACKAGE DIMENSIONS

TO-204AE (TO-3)
CASE 197A-05
ISSUE J



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.530 REF		38.86 REF	
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

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